

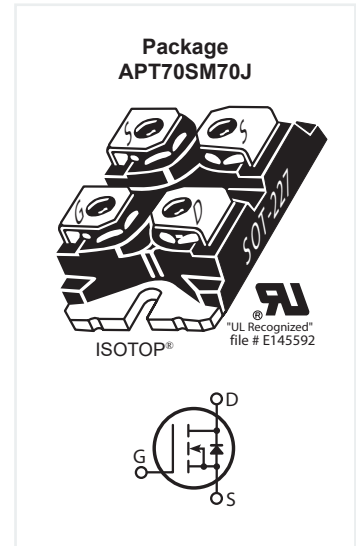
APT70SM70J

700V, 43A, 75mΩ

Silicon Carbide N-Channel Power MOSFET

DESCRIPTION

Silicon carbide (SiC) power MOSFET product line from Microsemi increase your performance over silicon MOSFET and silicon IGBT solutions while lowering your total cost of ownership for high-voltage applications.



FEATURES / TYPICAL APPLICATIONS

SiC MOSFET Features:

- Low on-resistance virtually independent on the ambient temperature
- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, $T_{j(max)} = +175C$
- Fast and reliable body diode
- Superior avalanche ruggedness

SiC MOSFET Benefits:

- High efficiency to enable lighter/compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need of external Free Wheeling Diode
- Lower system cost of ownership

Applications:

- PV inverter, converter and industrial motor drives
- Smart grid transmission & distribution
- Induction heating, and welding
- H/EV powertrain and EV charger
- Power supply and distribution

MAXIMUM RATINGS

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain Source Voltage	700	V
I_D	Continuous Drain Current @ $T_c = 25^\circ C$	43	A
	Continuous Drain Current @ $T_c = 100^\circ C$	30	
I_{DM}	Pulsed Drain Current ^①	135	
V_{GS}	Gate-Source Voltage	-10 to +25	V
P_D	Total Power Dissipation @ $T_c = 25^\circ C$	165	W
	Linear Derating Factor	1.1	W/°C

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance		0.63	0.91	°C/W
T_j	Operating Junction Temperature	-55		175	°C
T_{stg}	Storage Junction Temperature Range	-55		150	
W_T	Package Weight			1.03	oz
Torque	Mounting Torque (SOT-227 Package), 6-32 or M3 screw		5	10	in·lbf
			.56	1.13	N·m

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STATIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 1mA$	700			V
$R_{DS(on)}$	Drain-Source On Resistance ^②	$V_{GS} = 20V, I_D = 30A$		75	90	mΩ
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1mA$	1.7	2.5		V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold Voltage Temperature Coefficient			-4.9		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 700V$ $V_{GS} = 0V$	$T_J = 25^\circ C$		100	μA
			$T_J = 150^\circ C$		250	
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = +20V / -10V$			±100	nA
ESR	Equivalent Series Resistance	$f = 1MHz, 25mV, \text{Drain Short}$		0.97		Ω

$T_J = 25^\circ C$ unless otherwise specified

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit	
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DD} = 700V$ $f = 1MHz$		1935		pF	
C_{riss}	Reverse Transfer Capacitance			45			
C_{oss}	Output Capacitance			240			
Q_g	Total Gate Charge	$V_{GS} = 0/20V$		120		nC	
Q_{gs}	Gate-Source Charge	$V_{DD} = 466V$		20			
Q_{gd}	Gate-Drain Charge	$I_D = 30A$		34			
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 466V$ $V_{GS} = 0/20V$ $I_D = 30A$ $R_G = 3.0 \Omega$ ^③ $L = 115 \mu H$ $T_c = 25^\circ C$ Freewheeling Diode = APT10SCE65B		11		ns	
t_r	Current Rise Time			9			
$t_{d(off)}$	Turn-Off Delay Time			34			
t_f	Current Fall Time			20			
E_{on2}	Turn-On Switching Energy ^④	$V_{DD} = 466V$ $V_{GS} = 0/20V$ $I_D = 30A$ $R_G = 3.0 \Omega$ ^③ $L = 115 \mu H$ $T_c = 150^\circ C$ Freewheeling Diode = APT10SCE65B		291		μJ	
E_{off}	Turn-Off Switching Energy			122			
$t_{d(on)}$	Turn-On Delay Time			10			ns
t_r	Current Rise Time			9			
$t_{d(off)}$	Turn-Off Delay Time		37				
t_f	Current Fall Time		24				
E_{on2}	Turn-On Switching Energy ^④			257		μJ	
E_{off}	Turn-Off Switching Energy			135			

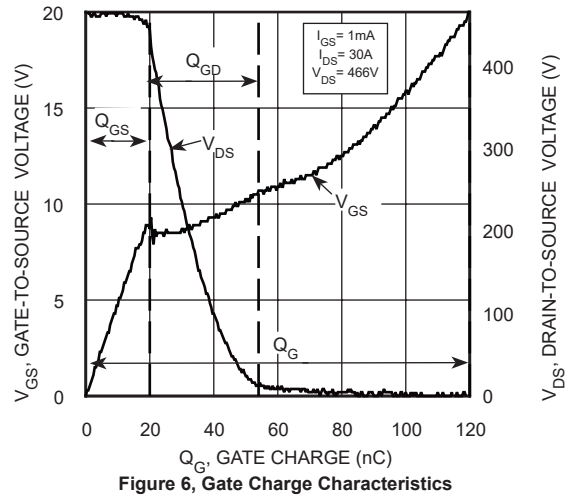
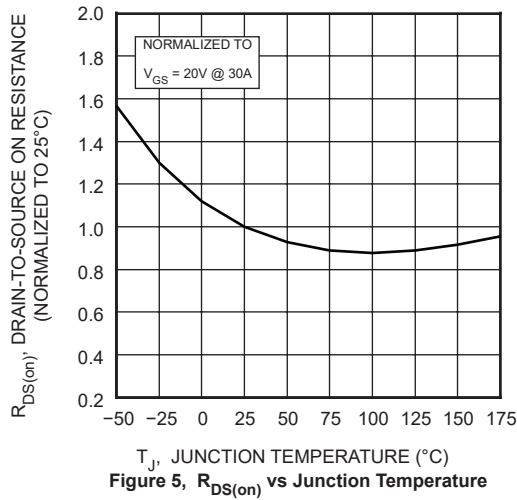
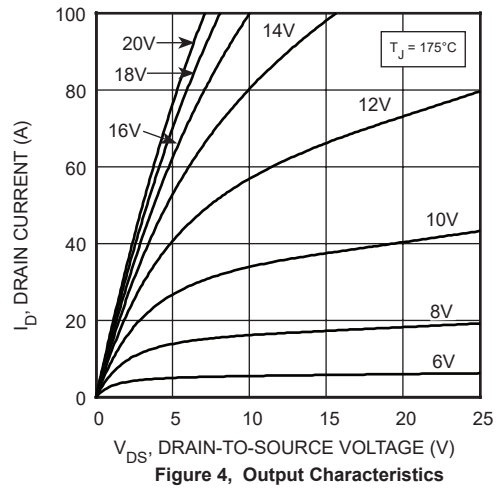
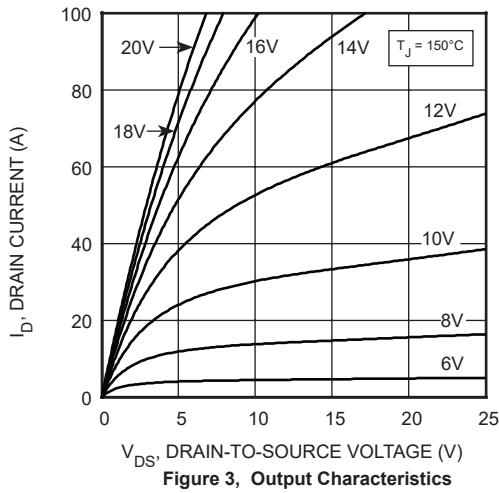
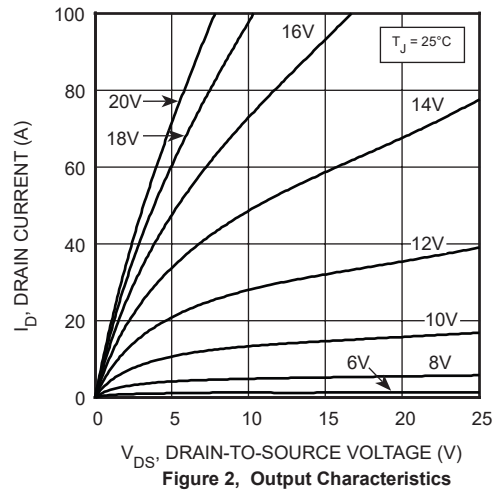
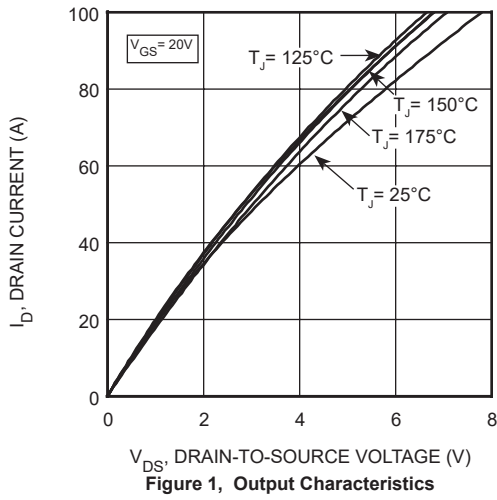
Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode Forward Voltage	$I_{SD} = 30A, V_{GS} = 0V$		4.45		V
t_{rr}	Reverse Recovery Time	$I_{SD} = 30A, V_{DD} = 466V$ $di/dt = -1000A/\mu s$		66		ns
Q_{rr}	Reverse Recovery Charge			320		nC
I_{rrm}	Reverse Recovery Current			10		A

$T_J = 25^\circ C$ unless otherwise specified

- ① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature
 ② Pulse test: Pulse Width < 380μs, duty cycle < 2%.
 ③ R_G is total gate resistance including internal gate driver impedance.
 ④ E_{on2} includes energy of APT20SCE65B free wheeling diode.

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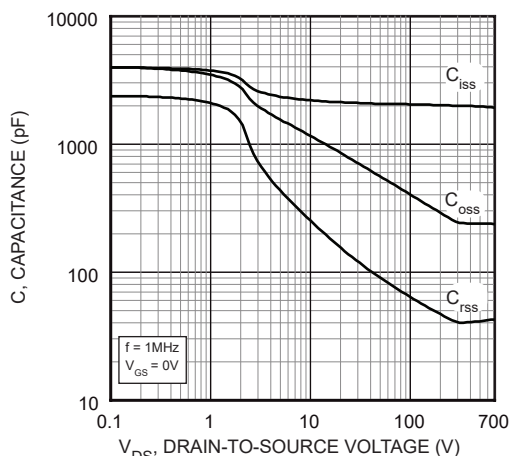


Figure 7, Capacitance vs Drain-to-Source Voltage

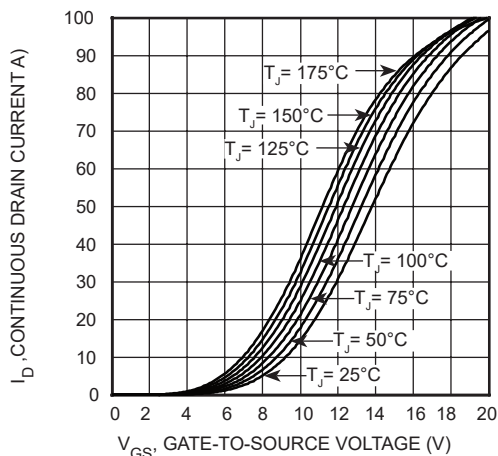


Figure 8, Output Characteristics I_D vs V_{GS} Temperature

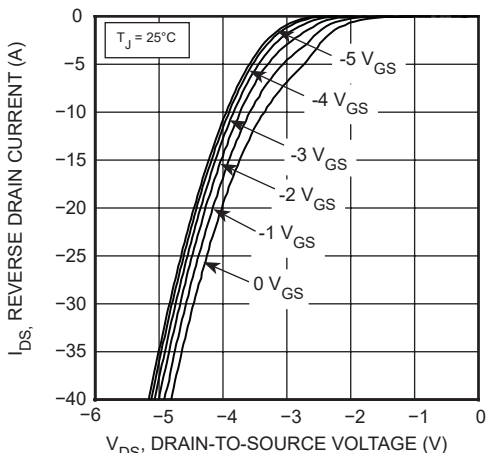


Figure 9, Reverse Drain Current vs Drain-to-Source Voltage Third Quadrant Conduction

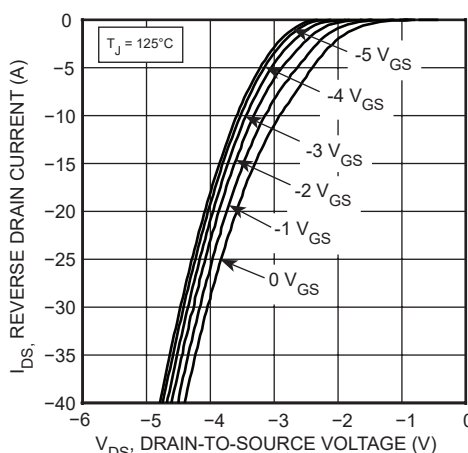


Figure 10, Reverse Drain Current vs Drain-to-Source Voltage Third Quadrant Conduction

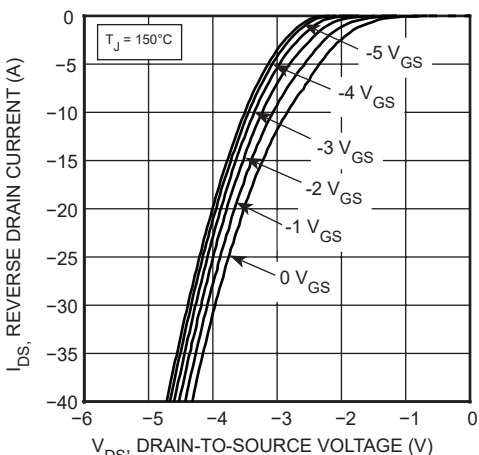


Figure 11, Reverse Drain Current vs Drain-to-Source Voltage Third Quadrant Conduction

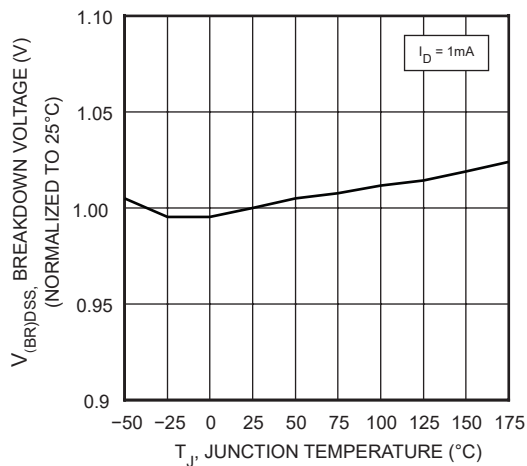


Figure 12, Breakdown Voltage vs Temperature

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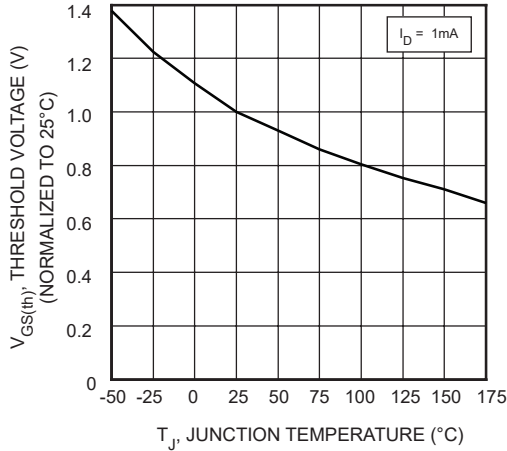


Figure 13, Threshold Voltage vs Temperature

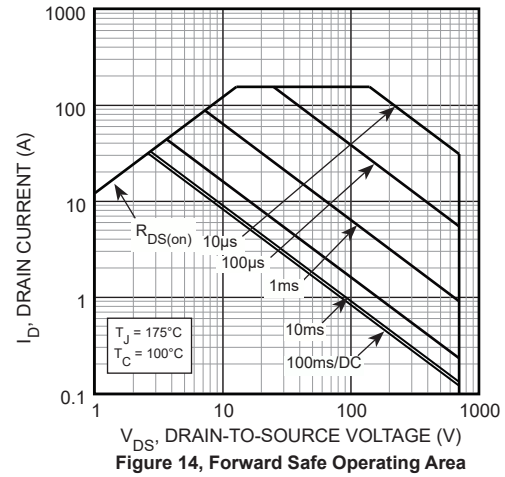


Figure 14, Forward Safe Operating Area

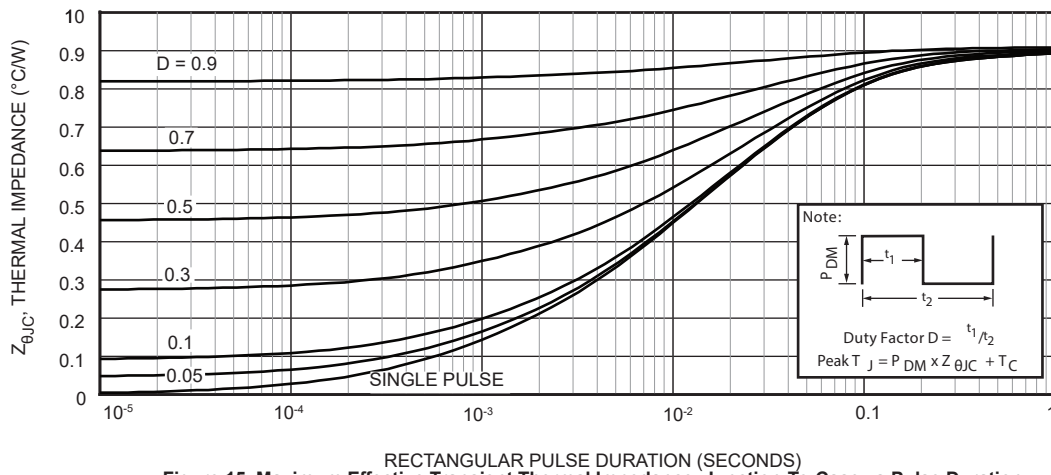
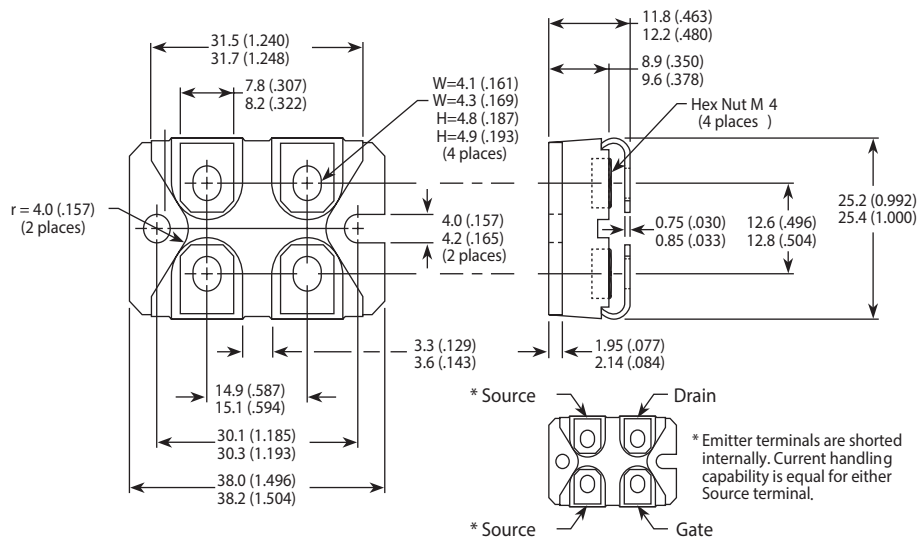


Figure 15, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters (Inches)

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